



Docket No.: YOR920030231US2

20140/00339US1 (PATENT)

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Patent Application of:

David B. Mitzi et al.

Application No.: 10/801,766

Confirmation No.: 6935

Filed: March 16, 2004

Art Unit: 2814

For:

HYDRAZINE-FREE SOLUTION

DEPOSITION OF CHALCOGENIDE FILMS

Examiner: Long Pham

INFORMATION DISCLOSURE STATEMENT (IDS)

Commissioner for Patents P.O. Box 1450 Alexandria, VA 22313-1450

Dear Sir:

Pursuant to 37 CFR 1.56, 1.97 and 1.98, the attention of the Patent and Trademark Office is hereby directed to the references listed on the attached PTO/SB/08. It is respectfully requested that the information be expressly considered during the prosecution of this application, and that the references be made of record therein and appear among the "References Cited" on any patent to issue therefrom.

This Information Disclosure Statement is filed prior to a first office action on the merits as far as known to the undersigned.

A copy of each reference on the PTO/SB/08 is attached except for the cited US Patent.

In accordance with 37 CFR 1.97(g), the filing of this Information Disclosure Statement shall not be construed to mean that a search has been made or that no other material information as defined in 37 CFR 1.56(a) exists. In accordance with 37 CFR 1.97(h), the filing of this Information Disclosure statement shall not be construed to be an admission that any patent,

publication or other information referred to therein is "prior art" for this invention unless specifically designated as such.

It is submitted that the Information Disclosure Statement is in compliance with 37 CFR 1.98 and the Examiner is respectfully requested to consider the listed references.

The Director is hereby authorized to charge any deficiency in the fees filed, asserted to be filed or which should have been filed herewith (or with any paper hereafter filed in this application by this firm) to our Deposit Account No. 22-0185, under Order No. 20140-00339-US.

Dated: 8 - (6 - 95

Respectfully submitted,

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PTO/SB/08a/b (08-03) Approved for use through 07/31/2006. OMB 0551-0031
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Complete if Known Substitute for form 1449A/B/PTO Application Number 10/801,766 INFORMATION DISCLOSURE Filing Date March 16, 2004 STATEMENT BY APPLICANT First Named Inventor David B Mitzi Art Unit 2814 (Use as many she ets as necessary) Examiner Name Long Pham Sheet 1 of 1 Attorney Docket Number 20140-00339-US1

U.S. PATENT DOCUMENTS					
Examiner Initials*	Cite	Document Number Number-Kind Code ² (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
	AA		04-30-2002	Vecht et al.	riguies Appeal

FOREIGN PATENT DOCUMENTS						
Examiner Initials*	Cite No.1	Foreign Patent Document Country Code ³ -Number ⁴ -Kind Code ⁵ (<i>if known</i>)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	
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		NON PATENT LITERATURE DOCUMENTS	
Examiner Initials	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T²
	CA	"The Use of Soluble Metal-Polyselenide Complexes as Precursors to Binary and Ternary Solid Metal Selenides" by Dhingra et al., Mat. Res. Soc. Symp. Proc. Vol. 180, 1990, pages 825-830	
	СВ	"Successive ionic layer adsorption and reaction (SILAR) method for the deposition of large area (~10cm²) tin disulfide (SnS₂) thin films" Sankapal et al., Materials Research Bulletin 35 (2000) pages 2027-2035	
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	CE	"Spin-coated amorphous chalcogenide films" Chern et al., J. Appl. Phys. 53 (10), October 1982, pages 6979-6982	
	CF	"Spin-Coating of MoS ₂ Thin Films" Pütz et al., Institut für Neue Materialien - INM, Department of Coating Technology, Im Stadtwald, Geb. 43, D-66123 Saarbrücken, Germany, 6 pages	
	CG	"Solution processed CdS thin film transistors" Schön et al., Thin Solid Films 385 (2001) pages 271-274	
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	CJ	"A Method for the Clean Syntheses of Sulfides/Selenides" II. Ternary Sulfides/Selenides, Marsh et al., Journal of the Electrochemical Society, 148 (7) pages D89-D93 (2001)	
	СК	"Electrical Characterization of 2H-SnS ₂ Single Crystals Synthesized by the Low Temperature Chemical Vapor Transport Method" Shibata et al., J. Phys. Chem. Solids Vol. 52, No. 3, pages 551-553, 1991	

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